# NPN Epitaxial Silicon Transistor

# KSC1008

#### **Features**

- Low-Frequency Amplifier Medium Speed Switching
- High Collector–Base Voltage: V<sub>CBO</sub> = 80 V
- Collector Current: I<sub>C</sub> = 700 mA
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)
- Non Suffix "-C" means Side Collector (1. Emitter 2. Base 3. Collector)
- Complement to KSA708
- These are Pb-Free Devices

#### **ABSOLUTE MAXIMUM RATINGS**

(T<sub>A</sub> = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>CEO</sub>	V <sub>CEO</sub> Collector–Emitter Voltage		V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
I <sub>C</sub>	Collector Current	700	mA
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise noted.) (Note 1)

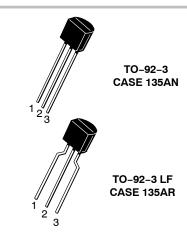
Symbol	Parameter	Value	Unit
P <sub>D</sub> Power Dissipation		800	mW
	Derate Above 25°C	6.4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	156	°C/W

1. PCB size: FR-4, 76 mm  $\times$  114 mm  $\times$  1.57 mm (3.0 inch  $\times$  4.5 inch  $\times$  0.062 inch) with minimum land pattern size.



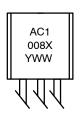
## ON Semiconductor®

www.onsemi.com



KSC1008: 1. Emitter 2. Base 3. Collector KSC1008C: 1. Emitter 2. Collector 3. Base

## **MARKING DIAGRAM**



A = Assembly Code
C1008 = Device Code
X = O/Y/YC/G
YWW = Date Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## KSC1008

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	80	-	_	V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	60	-	_	V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	8	-	_	V
I <sub>CBO</sub>	Collector Cut-Off Current	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0	_	-	0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-Off Current	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	_	-	0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 2 \text{ V}, I_{C} = 50 \text{ mA}$	40	-	400	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	_	0.2	0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	_	0.86	1.10	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 50 mA	30	50	_	MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	8	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## h<sub>FE</sub> Classification

Classification	0	Υ	G
hFE	70 ~ 140	120 ~ 240	200 ~ 400

## **ORDERING INFORMATION** (Note 2)

Part Number	Top Mark	Package	Shipping	
KSC1008OBU	C1008 O-	TO-92-3	10000 / Bulk Bag	
KSC1008YBU	C1008 Y-	(Pb-Free)	10000 / Bulk Bag	
KSC1008YTA	C1008 Y-	TO-92-3 LR	2000 / Fan-Fold	
KSC1008CYTA	C1008 YC	(Pb-Free)	2000 / Fan-Fold	
KSC1008GTA	C1008 G-		2000 / Fan-Fold	

<sup>2.</sup> Affix "-C-" means center collector pin. Affix "-O-, -Y-, -G-" means h<sub>FE</sub> classification. Suffix "-BU" means bulk packing, straight lead form. Suffix "-TA" means tape and ammo packing, 0.200 in-line spacing lead form.

## TYPICAL PERFORMANCE CHARACTERISTICS

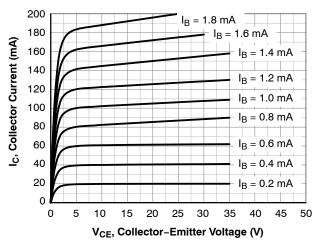


Figure 1. Static Characteristic

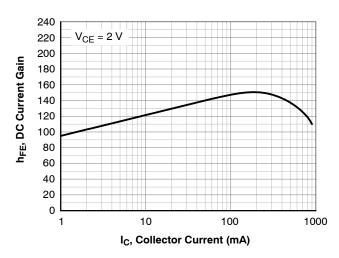


Figure 2. DC Current Gain

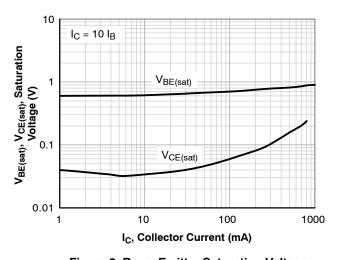


Figure 3. Base–Emitter Saturation Voltage and Collector–Emitter Saturation Voltage

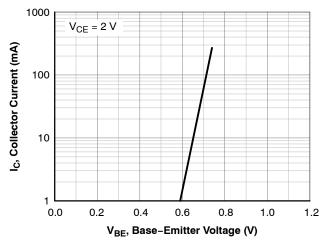


Figure 4. Base-Emitter On Voltage

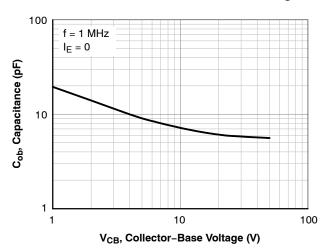
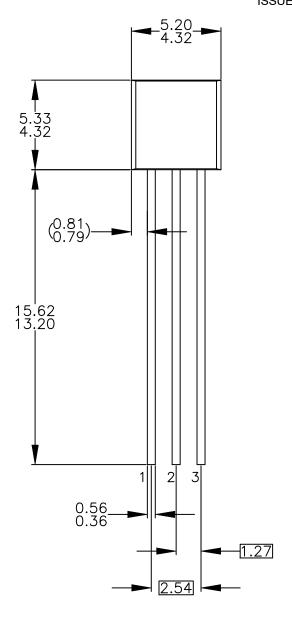
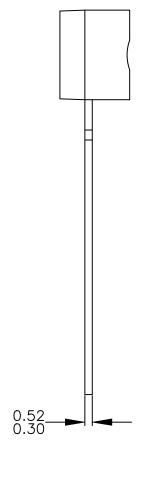


Figure 5. Collector Output Capacitance

## TO-92 3 4.825x4.76 CASE 135AN ISSUE O

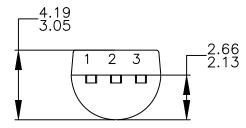
**DATE 31 JUL 2016** 





NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS. A)
- ALL DIMENSIONS ARE IN MILLIMETERS.
  DRAWING CONFORMS TO ASME Y14.5M—2009.



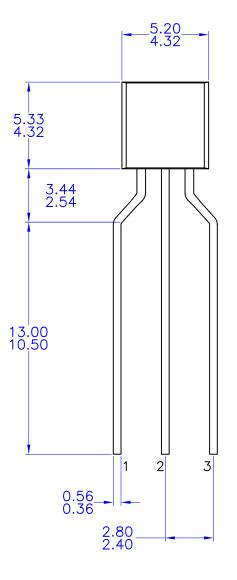
		98AON13880G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
	DESCRIPTION:	TO-92 3 4.825X4.76		PAGE 1 OF 1

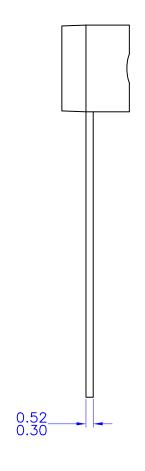
ON Semiconductor and III are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

## TO-92 3 4.83x4.76 LEADFORMED

CASE 135AR ISSUE O

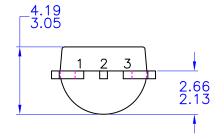
**DATE 30 SEP 2016** 





NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994



DOCUMENT NUMBER: 98AON13879G Electronic versions are uncontrolled except when accessed directly from the Document Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		, ,	
DESCRIPTION:	TO-92 3 4.83X4.76 LEADF	ORMED	PAGE 1 OF 1

ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA

2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR EMT2T2R

MCH6102-TL-E FP204-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E

NSV40301MZ4T1G NTE101 NTE13